

Application Serial No. 10/782,557  
Reply to office action of September 19, 2005

PATENT  
Docket: CU-3590

### Amendments To The Claims

The listing of claims presented below will replace all prior versions, and listings, of claims in the application.

#### Listing of claims:

1. (currently amended) A capacitor element configured to mount a semiconductor element thereon, said capacitor element comprising:

a base; and

a capacitor part provided on said base,

wherein said base is made of a resin whose coefficient of linear expansion is adjusted in accordance with a coefficient of linear expansion of the semiconductor element to fall within a range of 5 to 30 ppm/K.

2. (original) The capacitor element as claimed in claim 1, wherein the capacitor part includes two opposing electrodes and a dielectric layer interposed therebetween.

3. (currently amended) The capacitor element as claimed in claim 1, wherein the base is made of an epoxy resin including a filler for adjusting a coefficient of linear expansion of the epoxy resin ~~to fall within a range of 5-30 ppm/K.~~

4. (currently amended) The capacitor element as claimed in claim 1, wherein the base is made of a polyimide resin including a filler for adjusting a coefficient of linear expansion of the polyimide resin ~~to fall within a range of 5-30 ppm/K.~~

5. (currently amended) The capacitor element as claimed in claim 1, wherein the base is made of a thermoplastic liquid crystal polymer ~~whose coefficient of linear expansion is within a range of 5-30 ppm/K.~~

6. (currently amended) The capacitor element as claimed in claim 1, wherein the

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base is made of a resin including aramid fiber for adjusting a coefficient of linear expansion of the resin ~~to fall within a range of 5-30 ppm/K.~~

7. (cancelled)

8. (currently amended) ~~In combination, the capacitor element as claimed in claim 1,~~ A combination of a capacitor element and a semiconductor element mounted on the capacitor element, wherein:

said capacitor element is configured to mount a semiconductor element thereon comprises a base and a capacitor part provided on said base; and

said base is made of a resin whose coefficient of linear expansion is adjusted in accordance with a coefficient of linear expansion of the semiconductor element.

9-10. (cancelled)

11. (currently amended) A semiconductor device substrate on which a semiconductor element having on a substrate may be mounted, said semiconductor device substrate comprising:

a substrate body having a bottom surface that serves as a mounting surface in which external connection terminals are arranged; and

a capacitor element including:

a base made of a resin whose coefficient of linear expansion is adjusted in accordance with the semiconductor element to be mounted to a value between a coefficient of linear expansion of the substrate body and a coefficient of linear expansion of the substrate of the semiconductor element;

a capacitor part including two opposing electrodes and a dielectric layer

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interposed therebetween;

a plurality of terminals in a top surface of the capacitor element; and

a plurality of terminals in a bottom surface of the capacitor element,

the capacitor element being embedded in the substrate body, a top surface of the capacitor element being exposed at a top surface of the substrate body and serving as a surface on which the semiconductor element may be mounted.

12. (currently amended) A semiconductor device, comprising:

a semiconductor device substrate as claimed in claim 11; and

a semiconductor element,

wherein the semiconductor element ~~being is~~ mounted on a top surface of the semiconductor device substrate at which the capacitor element is exposed.

13. (new) The semiconductor device as claimed in claim 12, wherein the resin has a coefficient of linear expansion close to the coefficient of linear expansion of the substrate of the semiconductor element.

14. (new) The semiconductor device as claimed in claim 13, wherein the substrate of the semiconductor element is made of silicon.

15. (new) The semiconductor device as claimed in claim 12, wherein the resin has a coefficient of linear expansion in a range of 5 to 30 ppm/K.

16. (new) The semiconductor device substrate as claimed in claim 11, wherein the resin has a coefficient of linear expansion close to the coefficient of linear expansion of the substrate of the semiconductor element.

17. (new) The semiconductor substrate as claimed in claim 11, wherein the resin has a coefficient of linear expansion in a range of 5 to 30 ppm/K.